

Appln No. 09/693,484  
Amdt. Dated March 23, 2004  
Reply to Office action of December 31, 2003

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**Amendments to the Claims:**

Amend the claim set, replacing all prior versions, without prejudice or disclaimer of the subject matter thereof, as detailed in the following complete listing of all claims:

1. (Currently amended) A method of manufacturing an integrated circuit carrier (10), the method including the steps of:  
providing a substrate (46);  
demarcating at least one receiving zone (12) for receiving an integrated circuit or chip (14) on the substrate (46), the integrated circuit electrically associating with a plurality of electrical contacts (42) within the at least one receiving zone, and a plurality of island-defining portions (16) arranged about said at least one receiving zone (12);  
forming an electrical terminal (18) on island-defining portions (16), each electrical terminal (18) being electrically connected to one or more of the plurality of electrical contacts (42) within the at least one receiving zone (12); and  
creating one or more serpentine members (22) between neighboring island-defining portions (16) by removing material from the substrate (46), thereby reducing thermal strains involving the said island-defining portions (16).
2. (Currently amended) The method of claim 1, which includes forming electrical contacts (42) in said at least one receiving zone (12) and forming an electrical terminal (18) in each island-defining portion (16), each electrical terminal (18) being electrically connected via a track (52) of a circuitry layer (48) to one of the electrical contacts (42).
3. (Previously presented) The method of claim 2 which includes forming the circuitry layer (48) on a surface of the substrate (46) by depositing a metal layer on the substrate (46).
4. (Cancelled)
5. (Cancelled)
6. (Previously presented) The method of claim 1 which includes creating the one or more serpentine members (22) by etching through the substrate (46).

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7. (Previously presented) The method of claim 1 which includes forming the substrate (46) from a wafer of undoped silicon having an insulating layer (54).

8. (Previously presented) The method of claim 1 which includes demarcating said at least one receiving zone (12) by forming a recess in the substrate (46).

9. (Previously presented) The method of claim 8 which includes forming the recess by etching the substrate (46).

10. (Cancelled)

11. (Cancelled)